

SANYO	No.3467	2SK1464
		N-Channel MOS Silicon FET
Very High-Speed Switching Applications		

Features

- Low ON-state resistance.
- Very high-speed switching.
- Converters.

Absolute Maximum Ratings at Ta = 25°C

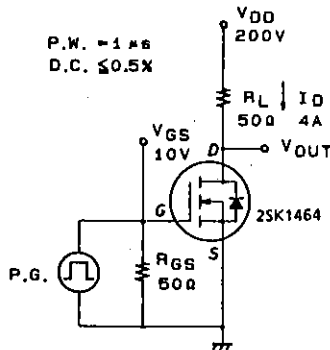
			unit
Drain to Source Voltage	V _{DS}	900	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current(DC)	I _D	8	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10 μs, duty cycle ≤ 1%	16 A
Allowable Power Dissipation	P _D	Tc = 25°C	80 W
Channel Temperature	T _{ch}		3.0 W
Storage Temperature	T _{stg}		150 °C
			-55 to +150 °C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	900			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 900V, V _{GS} = 0			1.0	mA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0			±100	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	2.0		3.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 20V, I _D = 4A	2.5	5.0		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = 4A, V _{GS} = 10V		1.2	1.6	Ω
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz		1600		pF
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz		500		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz		350		pF
Turn-ON Delay Time	t _{d(on)}	I _D = 4A, V _{GS} = 10V V _{DD} = 200V, R _{GS} = 50Ω		20		ns
Rise Time	t _r			80		ns
Turn-OFF Delay Time	t _{d(off)}			350		ns
Fall Time	t _f			150		ns
Diode Forward Voltage	V _{SD}	I _S = 8A, V _{GS} = 0			1.8	V

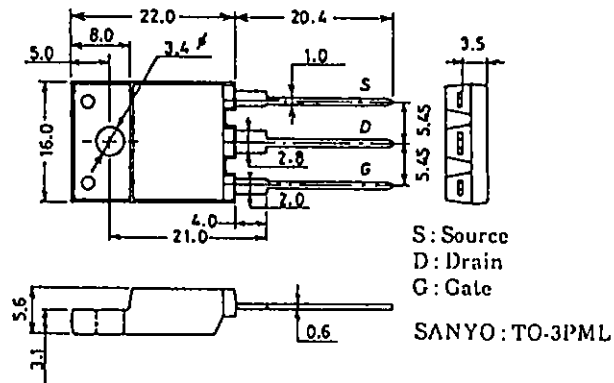
(Note) Be careful in handling the 2SK1464 because it has no protection diode between gate and source.

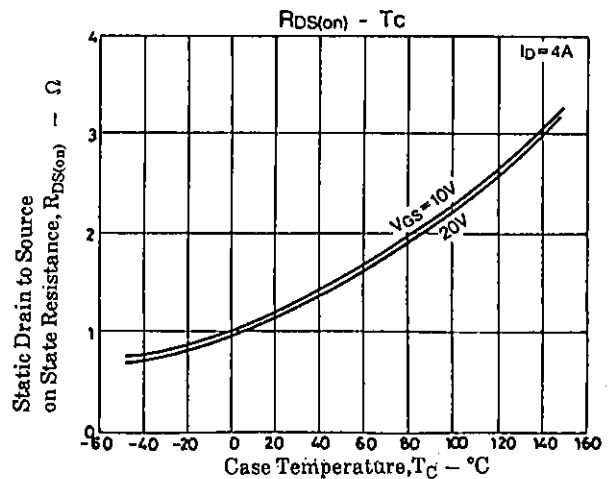
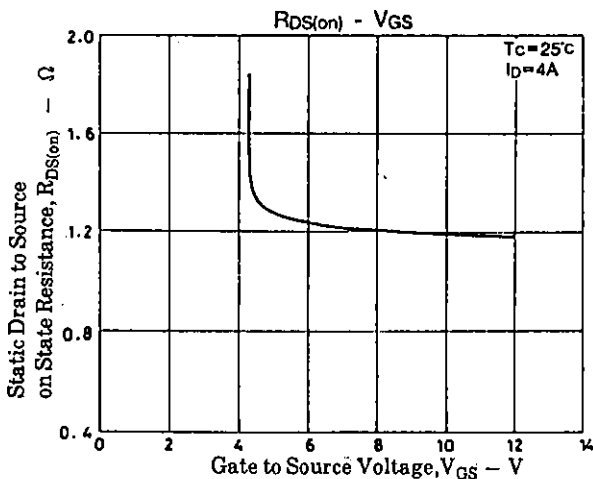
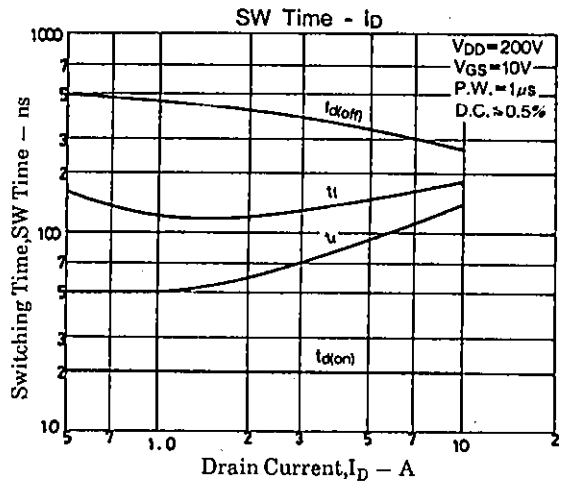
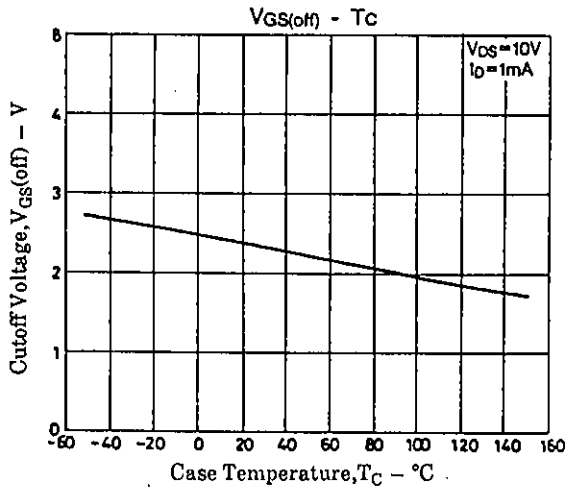
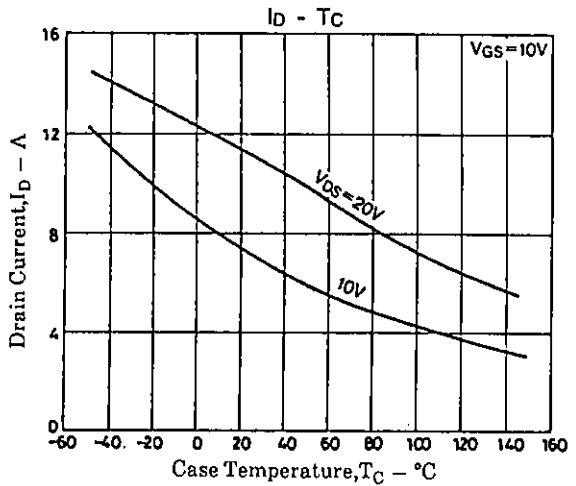
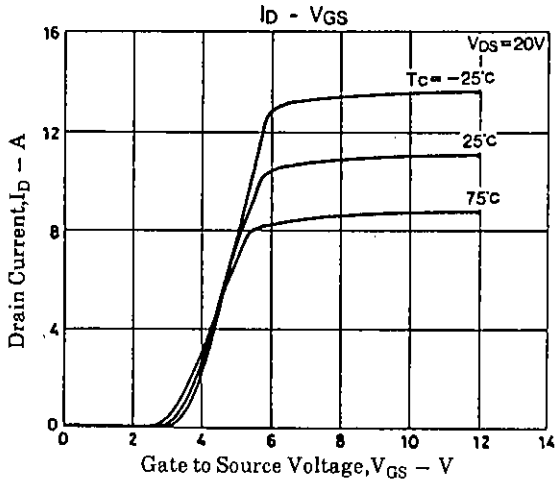
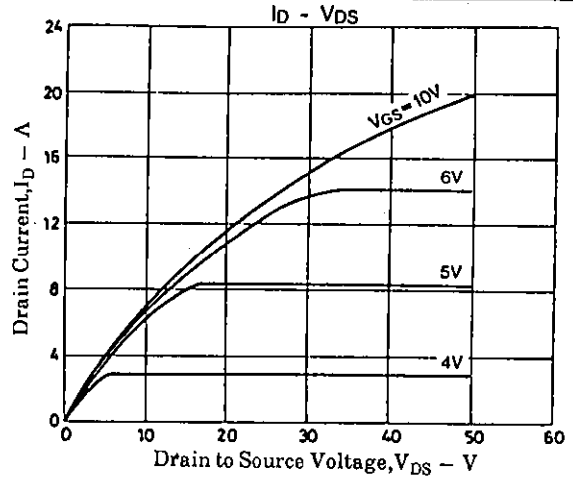
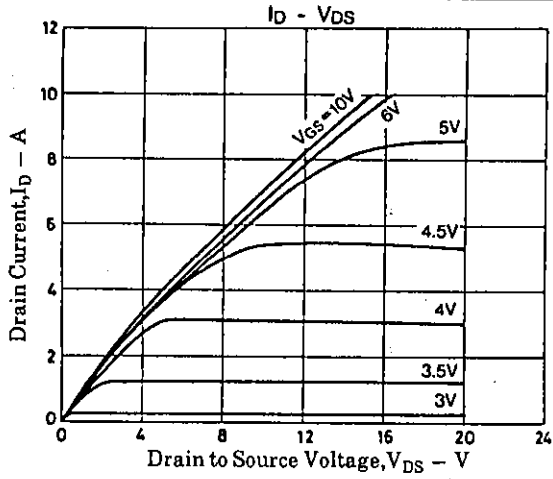
Switching Time Test Circuit

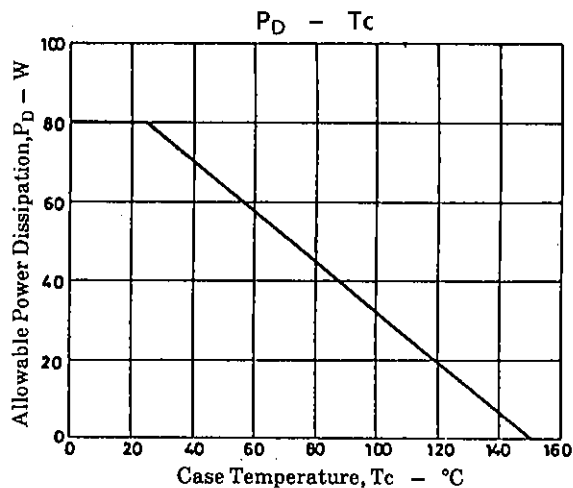
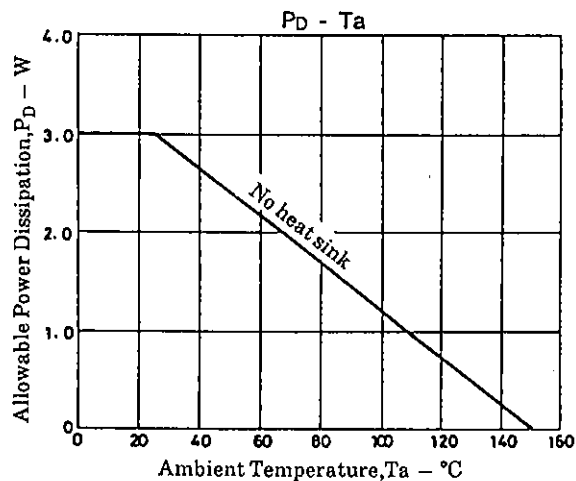
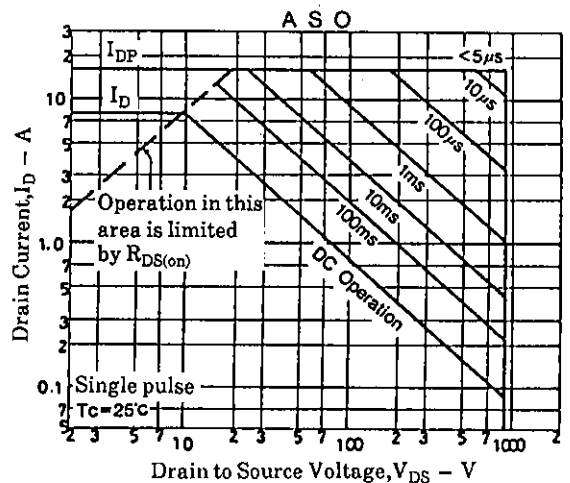
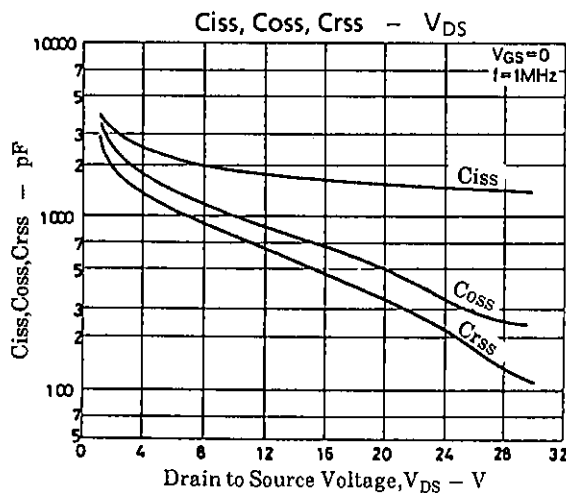
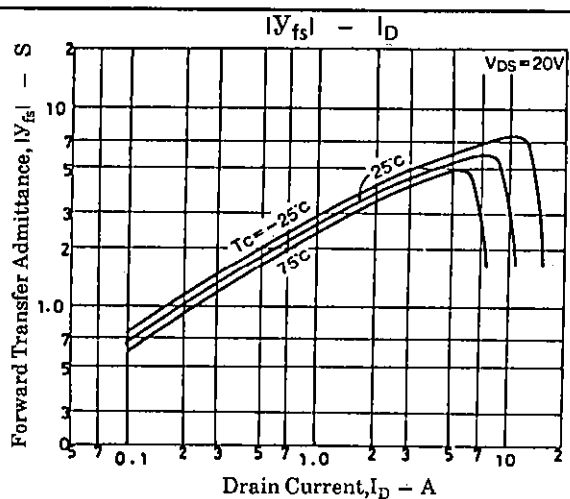
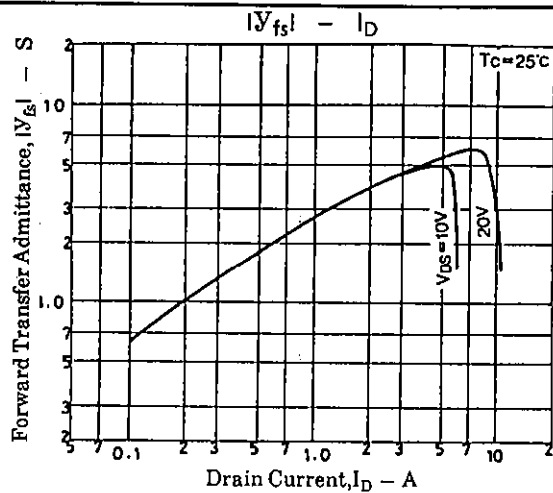


Package Dimensions 2076

(unit: mm)







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